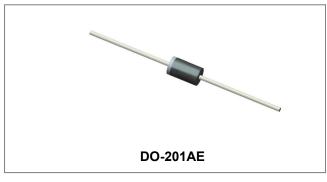






# **SBS5100 SCHOTTKY RECTIFIER**



#### **Features**

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters,
   Free Wheeling, and Polarity Protection Applications
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

## **Circuit Diagram**



### **Applications**

- · Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Disk drives
- Battery charging

### Maximum Ratings and Electrical Characteristics @T<sub>A</sub>=25°C unless otherwise specified

Characteristic	Symbol	SBS5100	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>R</sub> WM	100	V
Maximum RMS Voltage	V <sub>RMS</sub>	70	V
Average Rectified Output Current (Note 1) @T <sub>A</sub> = 105°C	I <sub>F(AV)</sub>	5.0	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	120	А
Forward Voltage $@I_F = 5.0A, T_A = 25^{\circ}C$ $@I_F = 5.0A, T_A = 125^{\circ}C$	V <sub>FM</sub>	0.85 0.70	V
Peak Reverse Current @T <sub>A</sub> = 25°C At Rated DC Blocking Voltage @T <sub>A</sub> = 125°C	I <sub>RM</sub>	0.5 10	mA
Maximum Junction Capacitance (Note 2)	Cj	250	pF
Typical Thermal Resistance Junction to Ambient	R <sub>θJA</sub>	25	K/W
Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 to +150	°C

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1MHz and applied reverse voltage of 5.0V D.C.

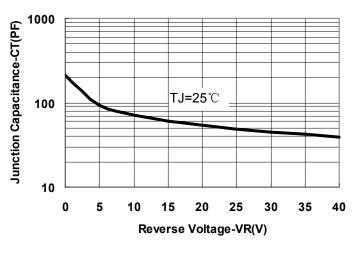
- China Germany Korea Singapore United States •
- http://www.smc-diodes.com
   sales@ smc-diodes.com







### **Ratings and Characteristics Curves**



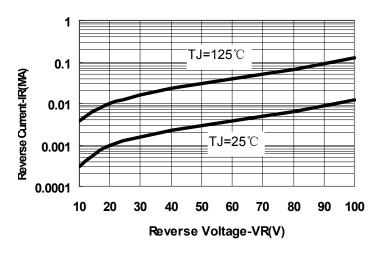


Fig.1-Typical Junction Capacitance

**Fig.2-Typical Reverse Current** 

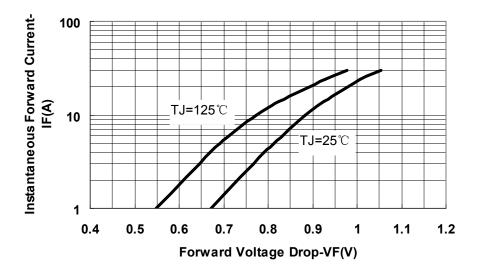


Fig.3-Typical Forward Voltage Drop Characteristics

<sup>•</sup> China - Germany - Korea - Singapore - United States •

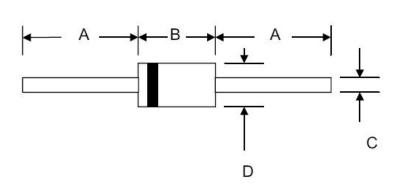
<sup>•</sup> http://www.smc-diodes.com - sales@ smc-diodes.com •







### **Mechanical Dimensions DO-201AE**



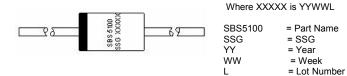
CVMDOI	Millimeters		Inches	
SYMBOL	Min.	Max.	Min.	Max.
А	25.4	-	1.000	-
В	7.20	9.50	0.283	0.374
С	0.94	1.07	0.037	0.042
D	4.80	5.30	0.189	0.209

# **Ordering Information**

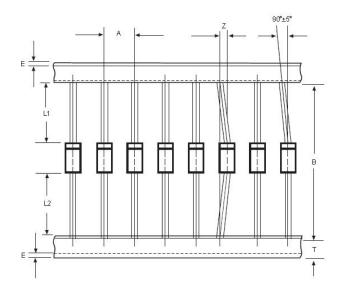
Device	Package	Shipping
SB5S100	DO-201AE	2000pag / tapa
	(Pb-Free)	3000pcs / tape

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

# **Marking Diagram**



## **Carrier Tape Specification DO-201AE**



SYMBOL	Millimeters		
STWIBOL	Min.	Max.	
А	9.50	10.50	
В	50.9	53.9	
Z	-	1.20	
Т	5.60	6.40	
Е	-	0.80	
IL1-L2I	-	1.0	

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